

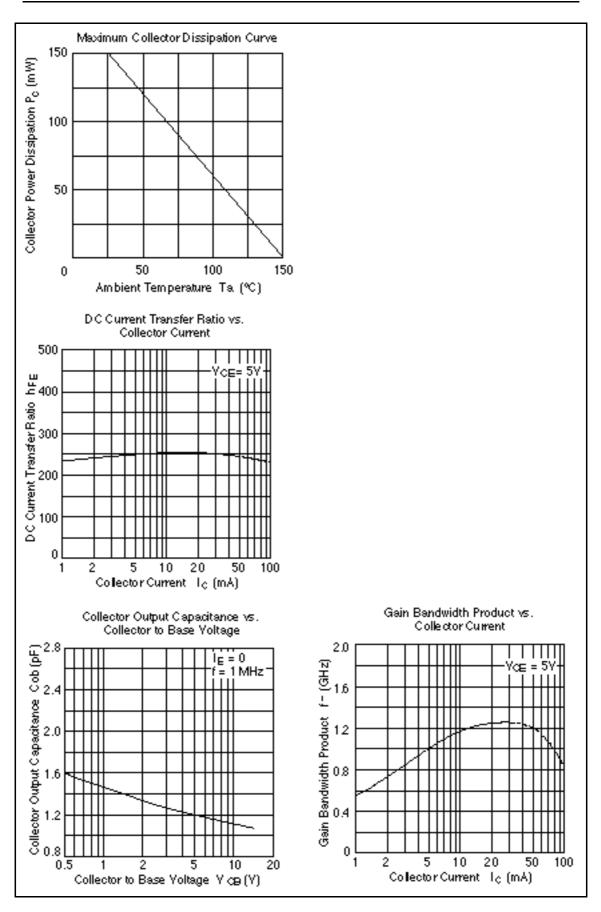
Absolute Maximum Ratings (Ta = 25° C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	12	V
Collector to emitter voltage	V _{CEO}	8	V
Emitter to base voltage	V _{EBO}	3	V
Collector current	I _c	100	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Тј	150	°C
Storage temperature	Tstg	–55 to +150	°C

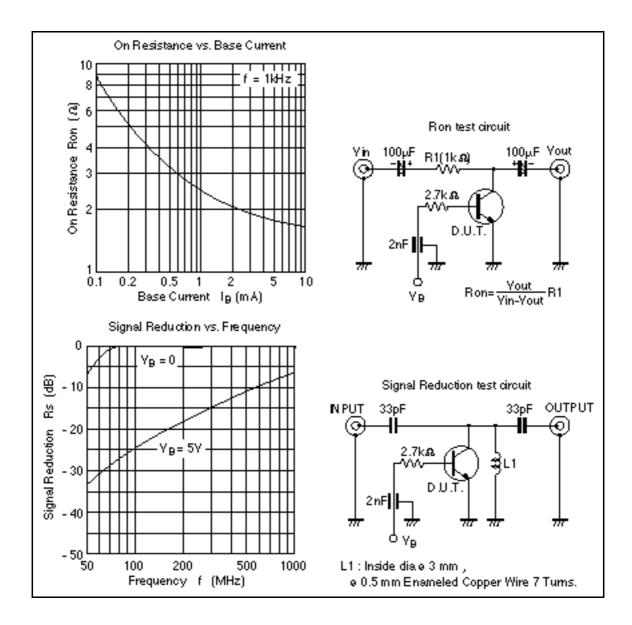
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	12	-	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I _{CBO}	—	—	1	μA	$V_{CB} = 10 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	1	mA	V_{ce} = 8 V, R_{be} =
Emitter cutoff current	I _{EBO}	_	_	10	μA	$V_{EB} = 3 V, I_{C} = 0$
DC current transfer ratio	h _{FE}	100	250	600		V_{ce} = 5 V, I_c = 5 mA
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	200	300	mV	$I_{c} = 80 \text{ mA}, I_{B} = 5 \text{ mA}$
Collector output capacitance	Cob	_	1.2	1.6	pF	$V_{_{CB}} = 5 \text{ V}, \text{ I}_{_{E}} = 0, \text{ f} = 1 \text{ MHz}$
On resistance	Ron		2.0			I _B = 2.5 mA, f = 1 kHz

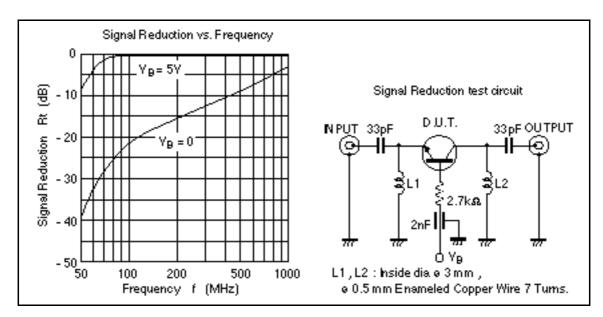
Note: Marking is "YV-".



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